

Abstract of the Disclosure (Fig. 1)**THIN FILM TRANSISTOR AND METHOD OF MANUFACTURING IT**

A thin film transistor comprises a source area (102) and a drain area (103) which are composed of a silicon thin film to which an impurity which serves as a donor or an acceptor is added, a channel area (104) composed of the silicon thin film formed between said source area and said drain area in contact with said source area and said drain area, a gate insulation film (107) formed in such a manner as to cover said source area, said drain area, and said channel area, and a gate electrode (108) disposed on said gate insulation film. The gate electrode does not overlap said source area or said drain area, allowing a high ON/OFF ratio to be realized. Described are various methods for producing such a thin film transistor.